

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
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Complete if Known

Application Number	10/786,354
Filing Date	February 25, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2818
Examiner Name	Huynh, Andy

Sheet 1 of 1

Attorney Docket No: 303.686US3

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
Ah	US-20010002333	05/31/2001	Huang, Chao-Yuan, et al.	438	637	03/29/1999
	US-1,254,987	01/29/1918	Cooper, H. S.			10/15/1917
	US-1,976,375	10/09/1934	Smith, J. K.	148	11.5	01/27/1931
	US20020109233	08/15/2002	Farrar, Paul A.	257	762	04/05/2002
	US-2,244,608	06/03/1941	Cooper, H. S.	75	138	02/09/1939
	US-2,842,438	07/08/1958	Saarivirta, M. J., et al.	75	153	08/02/1956
	US-3,147,110	09/01/1964	Foerster, G. S.	75	122.5	11/27/1961
	US-3,506,438	04/14/1970	Krock, R. H., et al.	75	208	07/24/1967
	US-3,548,948	12/22/1970	Richmond, W. J., et al.	164	68	01/23/1969
	US-3,687,737	08/29/1972	Krock, R. H., et al.	148	2	07/17/1970
	US-3,923,500	12/02/1975	Kitazawa, Kunio, et al.	75	156.5	09/04/1974
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	US-6,197,181	03/06/2001	Chen, Linlin	205	123	03/20/1998
	US-6,268,277	07/31/2001	Bang, D	438	619	07/16/1999
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Ah	JP-07078815 ^{With English Abstracts (Renewed EPO)}	03/20/1995	Miyamoto, I.	HO1	21/320 5	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Ah		"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", Brooks Instrument, http://www.frc.com/brooks/semiconductor/products1i.html , (1991), 1 page	

EXAMINER

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10/08/04

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown 10/786,354
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 1 of 13		Attorney Docket No: 303.686US3	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	US20020014646	02/07/2002	Tsu, , et al.	257	296	
	US20020028552	03/07/2002	Lee, , et al.	438	243	
	US20020096768	07/25/2002	Joshi, Rajiv Vasant	257	750	
	US-3,337,334	08/22/1967	Fenn, R. W., et al.	75	150	12/06/1963
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André Kueh

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(Use as many sheets as necessary)</small>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 2 of 13		Attorney Docket No: 303.686US3	

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EXAMINER

Andy Nguyen

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 3 of 13		Attorney Docket No: 303.686US3	

<i>Ch</i>	US-5,442,237	08/15/1995	Hughes, Henry G., et al.	257	759	02/04/1994
	US-5,444,015	08/22/1995	Aitken, John M., et al.	437	182	04/11/1994
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	US-5,470,801	11/28/1995	Kapoor, Ashok K., et al.	437	238	06/28/1993
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	US-5,485,037	01/16/1996	Marrs, R. C.	257	712	03/27/1995
	US-5,495,667	03/05/1996	Farnworth, Warren M., et al.	29	843	11/07/1994
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	US-5,534,731	07/09/1996	Cheung, Robin	257	759	10/28/1994
	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
	US-5,539,060	07/23/1996	Tsunogae, Y. , et al.	525	338	10/13/1995
	US-5,539,227	07/23/1996	Nakano, H.	257	276	08/02/1995
	US-5,578,146	11/26/1996	Grant, L. A., et al.	148	437	01/16/1996
	US-5,595,937	01/21/1997	Mikagi, K.	437	192	04/12/1996
	US-5,609,721	03/11/1997	Tsukune, A , et al.	156	646.1	01/03/1995
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	US-5,662,788	09/02/1997	Sandhu, G. , et al.	205	87	06/03/1996
	US-5,667,600	09/16/1997	Grensing, Fritz C., et al.	148	437	03/31/1994
	US-5,670,420	09/23/1997	Choi, Kyeong K.	437	189	11/08/1995
	US-5,674,787	10/07/1997	Zhao, Bin , et al.	437	230	01/16/1996
	US-5,675,187	10/07/1997	Numata, K. , et al.	257	758	05/16/1996
	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
	US-5,681,441	10/28/1997	Svendsen, Leo G., et al.	205	114	12/22/1992
	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
	US-5,705,425	01/06/1998	Miura, T. , et al.	437	182	04/26/1996
<i>Ch</i>	US-5,719,089	02/17/1998	Cherng, Meng-Jaw , et al.	438	637	06/21/1996
<i>Ch</i>	US-5,719,410	02/17/1998	Suehiro, S. , et al.	257	77	12/16/1996

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known				
		Application Number		Unknown		
		Filing Date		Even Date Herewith		
		First Named Inventor		Ahn, Kie		
		Group Art Unit		Unknown		
		Examiner Name		Unknown		
Sheet 4 of 13		Attorney Docket No: 303.686US3				

<i>Ar</i>	US-5,725,689	03/10/1998	Nishida, S. , et al.	148	320	10/05/1995
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	US-5,801,098	09/01/1998	Fiordalice, R. , et al.	438	653	09/03/1996
	US-5,814,557	09/29/1998	Venkatraman, Ramnath , et al.	438	622	05/20/1996
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	US-5,824,599	10/20/1998	Schacham-Diamond, Yosef , et al.	438	678	01/16/1996
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✓	US-5,891,797	04/06/1999	Farrar, P. A.	438	619	10/20/1997
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	US-5,893,752	04/13/1999	Zhang, J. , et al.	438	687	12/22/1997
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	US-5,897,370	04/27/1999	Joshi, R. V. , et al.	438	632	10/28/1996
	US-5,900,668	05/04/1999	Wollesen, D. L.	257	522	11/30/1995
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	US-5,933,758	08/03/1999	Jain, A.	438	687	05/12/1997
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	US-5,948,467	09/07/1999	Nguyen, T. , et al.	427	99	07/24/1998
	US-5,962,923	10/05/1999	Xu, Z. , et al.	257	774	08/07/1995
	US-5,968,333	10/19/1999	Nogami, T. , et al.	205	184	04/07/1998
	US-5,969,422	10/19/1999	Ting, C. , et al.	257	762	05/15/1997
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EXAMINER

Andrea Nguyen

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		Application Number	Unknown	
		Filing Date	Even Date Herewith	
		First Named Inventor	Ahn, Kie	
		Group Art Unit	Unknown	
		Examiner Name	Unknown	
Sheet 5 of 13		Attorney Docket No: 303.686US3		

<i>Ah</i>	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998
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	US-5,989,623	11/23/1999	Chen, Liang-Yuh , et al.	427	97	08/19/1997
<input checked="" type="checkbox"/>	US-5,994,776	11/30/1999	Fang, Peng , et al.	257	758	04/20/1998
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	US-6,015,738	01/18/2000	Levy, H. J., et al.	438	275	11/17/1997
	US-6,017,820	01/25/2000	Ting, C. H., et al.	438	689	07/17/1998
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		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
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		Group Art Unit		Unknown		
		Examiner Name		Unknown		
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		Application Number	Unknown
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		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
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		Application Number	Unknown
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		First Named Inventor	Ahn, Kie
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 13 of 13		Attorney Docket No: 303.686US3	

<i>Ah</i>	VENKATESAN, S. , et al., "A High Performance 1.8V, 0.20 micrometer CMOS Technology with Copper Metalization", <u>Electron Devices Meeting, 1997. Technical Digest., International</u> , (December 7-10, 1997),769-772	
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Andy Mayall

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